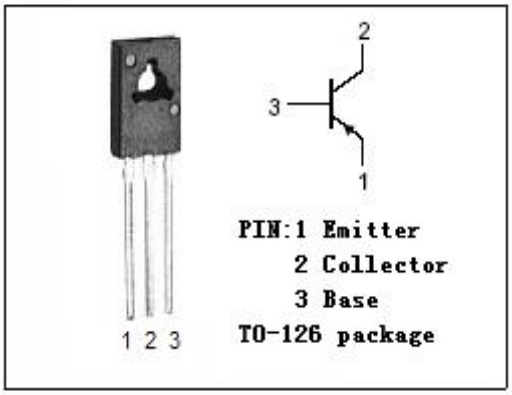
isc Silicon PNP Power Transistors — 2SB1436

DESCRIPTION

- Low Collector Saturation Voltage
- High Power Dissipation-
  : P_C= 5W(Max)@T_C=25℃
- Complement to Type 2SD2166
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

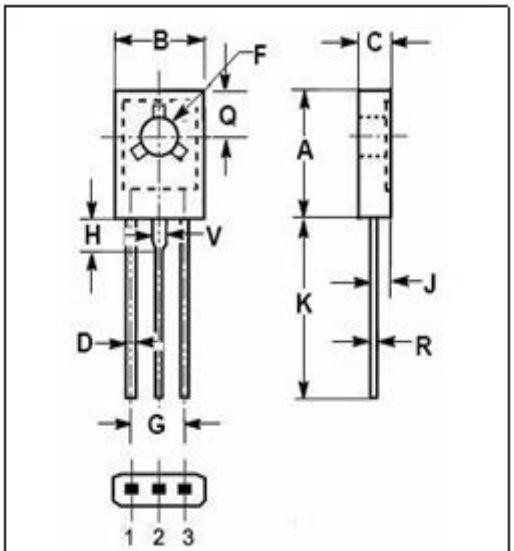


APPLICATIONS

- Designed for use in output stage of audio amplifier, voltage regulator, DC-DC converter and relay driver.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-20	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-5	A
I_{CM}	Collector Current-Pulse	-10	A
P_C	Collector Power Dissipation @T_C=25℃	5	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	mm MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -50 μA ; I_E= 0	-30			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -1mA ; I_B= 0	-20			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Vltage	I_E= -50 μA; I_C= 0	-6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -4A; I_B= -0.1A			-1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -20V; I_E= 0			-0.5	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-0.5	μA
h_{FE}	DC Current Gain	I_C= -0.5A; V_{CE}= -2V	180		390	
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -20V; f= 1MHz		60		pF
f_T	Current-Gain—Bandwidth Product	I_E= -50mA; V_{CE}= -6V		120		MHz